

FC21

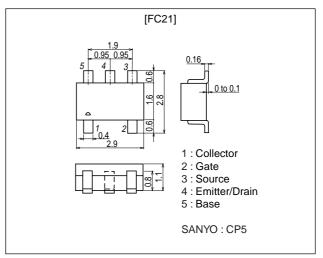
High-Frequency Amplifier, AM tuner RF Amplifier Applications

Features

 The FC21 contains both a 2SK1740 equivalent chip and a 2SC2812 equivalent chip in the CP package, thus realizes higher efficiency in device mounting on the PCB.

Package Dimensions

unit : mm 2122



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit					
[FET]									
Drain-to-Source Voltage	VDSX		40	V					
Gate-to-Drain Voltage	V _{GDS}		-40	V					
Gate Current	IG		10	mA					
Drain Current	ID		75	mA					
Allowable Power Dissipation	PD		400	mW					
[TR]									
Collector-to-Base Voltage	VCBO		55	V					
Collector-to-Emitter Voltage	VCEO		50	V					
Emitter-to-Base Voltage	VEBO		6	V					
Collector Current	Ic		150	mA					
Collector Current(Pulse)	ICP		300	mA					
Base Current	IB		30	mA					
Collector Dissipation	PC		200	mW					
[Common Ratings]	<u> </u>								
Total Dissipation	PT		600	mW					
Junction Temperature	Tj		150	°C					
Storage Temperature	Tstg		-55 to +150	°C					

Marking: 1C

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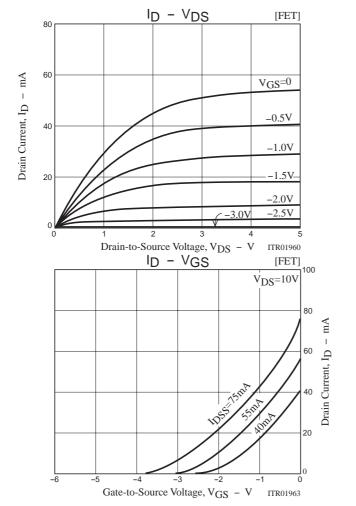
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Ratings		
Parameter		Conditions	min	typ	max	Unit
[FET]				,		
Gate-to-Drain Breakdown Voltage	V(BR)GDS	I _G =-10μA, V _{DS} =0	-40			V
Gate Cutoff Current	IGSS	VGS=-20V, VDS=0			-1.0	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =100μA	-2.0	-3.0	-5.0	V
Drain Current	IDSS	V _{DS} =10V, V _{GS} =0	40*		75*	mA
Forward Transfer Admittance	yfs	VDS=10V, VGS=0, f=1kHz		30		mS
Input Capacitance	Ciss	V _{DS} =10V, V _{GS} =0, f=1MHz		11		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, V _{GS} =0, f=1MHz		2.5		pF
Noise Figure	NF	V _{DS} =10V, Rg=1kΩ, I _D =1mA, f=1kHz		1.5		dB
[TR]	•					
Collector Cutoff Current	ICBO	V _{CB} =35V, I _E =0			0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0			0.1	μΑ
DC Current Gain	hFE	V _{CE} =6V, I _C =1mA	135		600	
Gain-Bandwidth Product	fŢ	V _{CE} =6V, I _C =10mA		100		MHz
Output Capacitance	Cob	V _{CB} =6V, f=1MHz		3		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=50mA, IB=5mA		0.1	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=50mA, IB=5mA		0.8	1.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0	55			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0	6			V

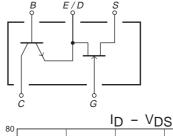
*: The FC21 is classified by IDSS as follows: (unit: mA)

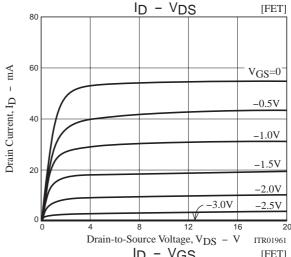
Rank	J	K	L							
IDSS	40 to 52	48 to 63	57 to 75							

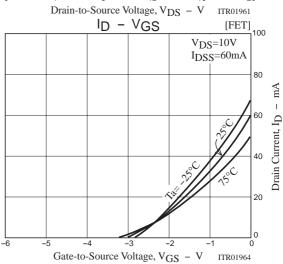
The specifications shown above are for each individual FET or transistor.

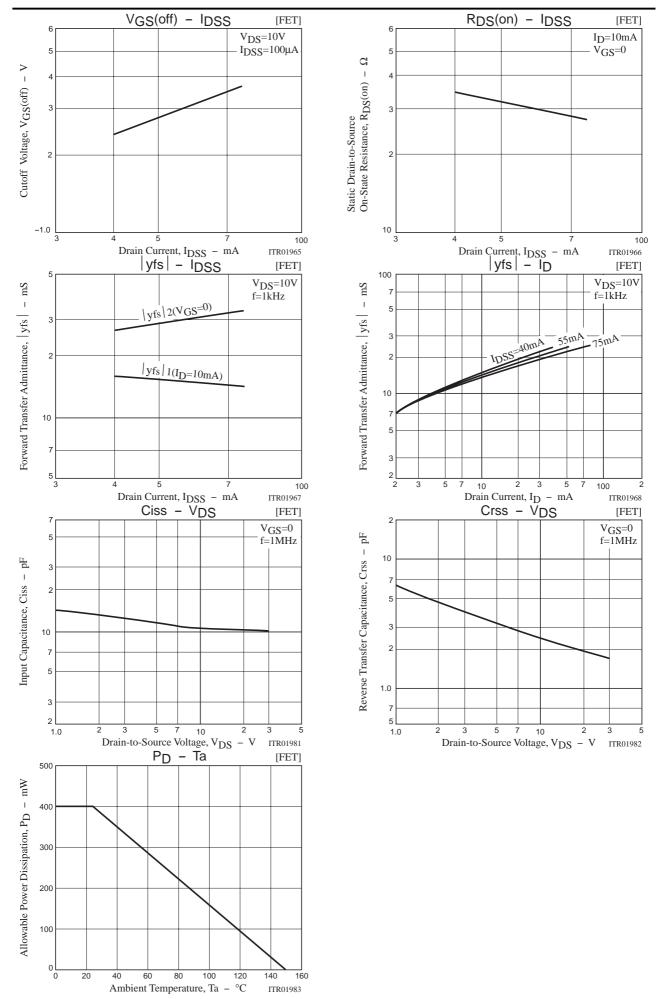


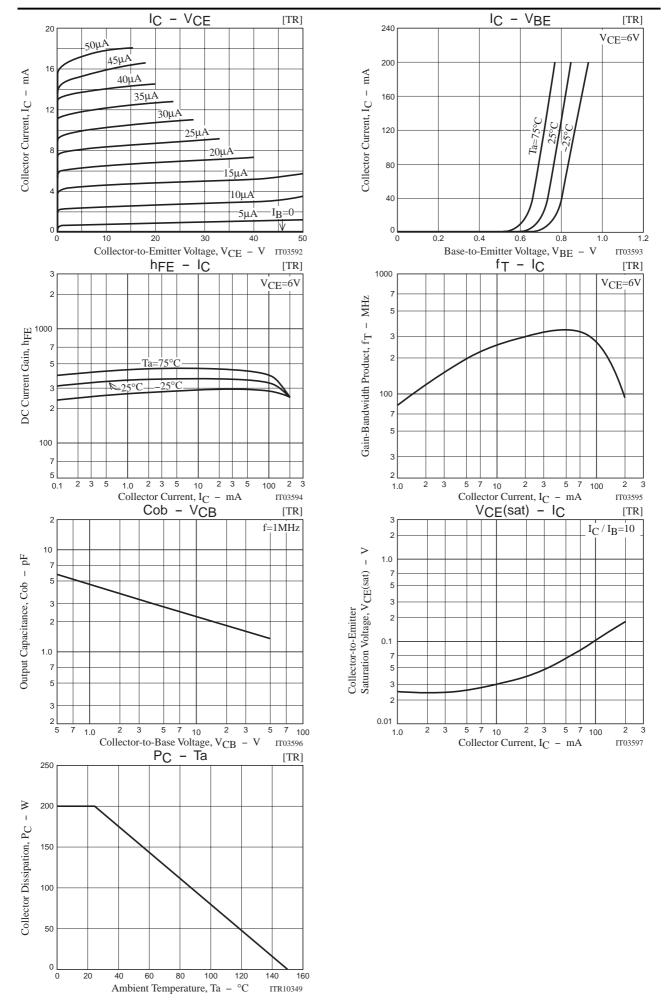












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